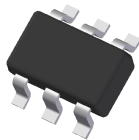


Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(TH)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

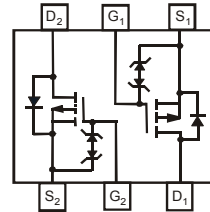


TOP VIEW

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)

SOT-363


 TOP VIEW
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 8	V
Drain Current (Note 1)	I_D	$T_A = 25^\circ C$	-430
		$T_A = 85^\circ C$	-310

Thermal Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_d	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ C/W$
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ C$

Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0V, I_D = -250mA$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 1.0	μA	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	0.7	0.9	Ω	$V_{GS} = -4.5V, I_D = -430mA$
		—	1.1	1.4		$V_{GS} = -2.5V, I_D = -300mA$
		—	1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	$ Y_{fs} $	200	—	—	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 4)	V_{SD}	-0.5	—	-1.2	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	175	pF	$V_{DS} = -16V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	20	pF	

- Notes:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Short duration pulse test used to minimize self-heating effect.

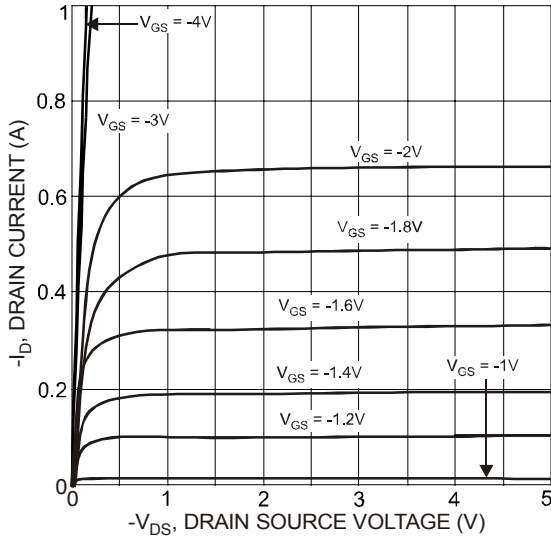


Fig. 1 Typical Output Characteristics

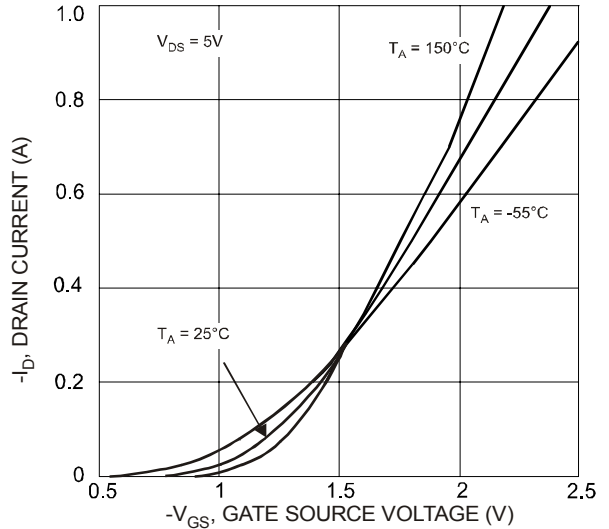


Fig. 2 Typical Transfer Characteristics

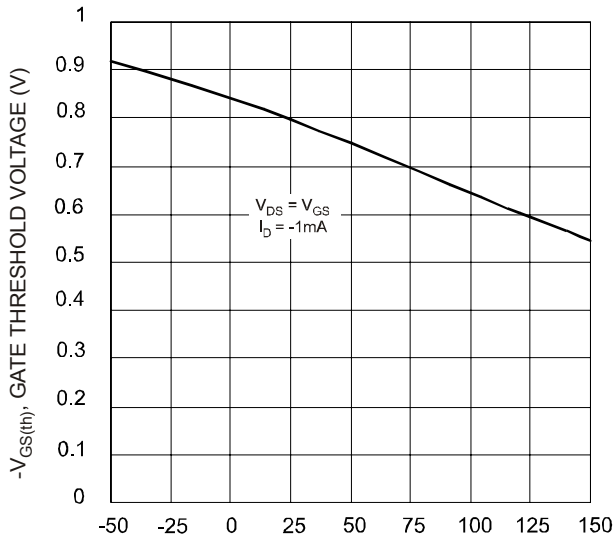


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

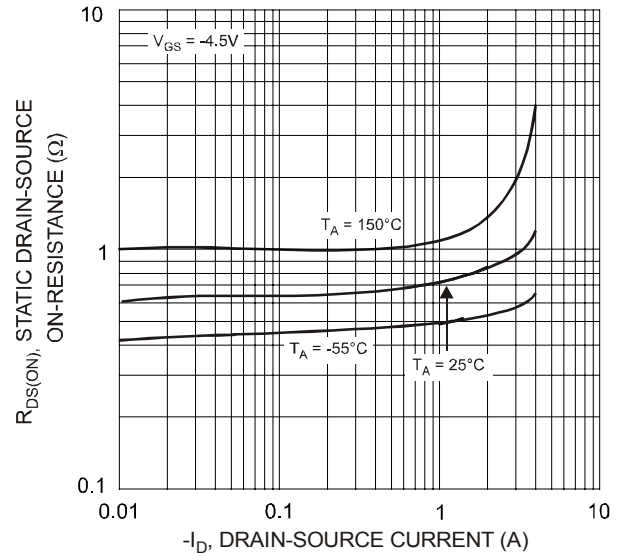


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

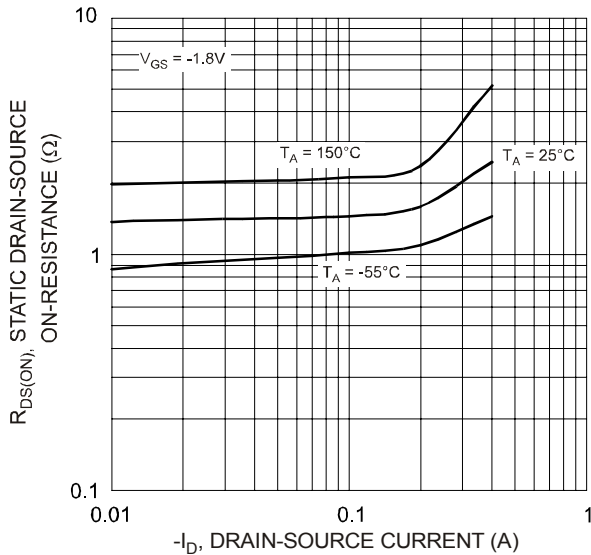


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

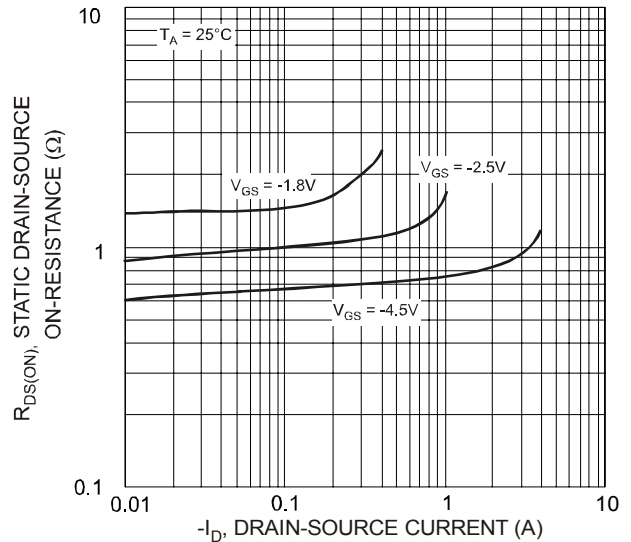


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

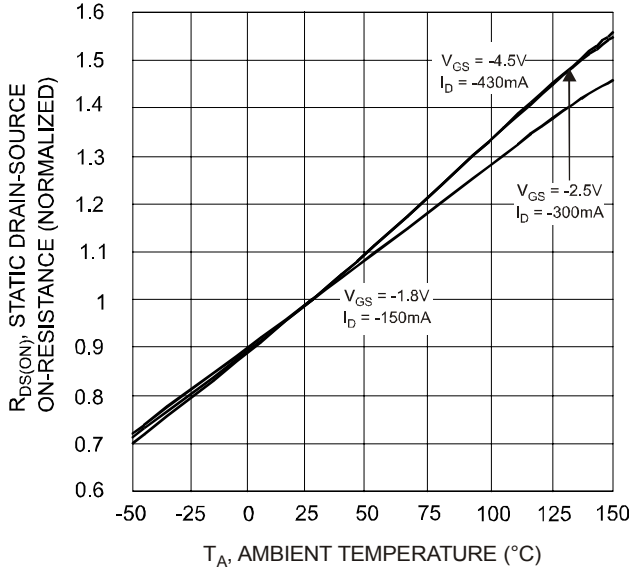


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

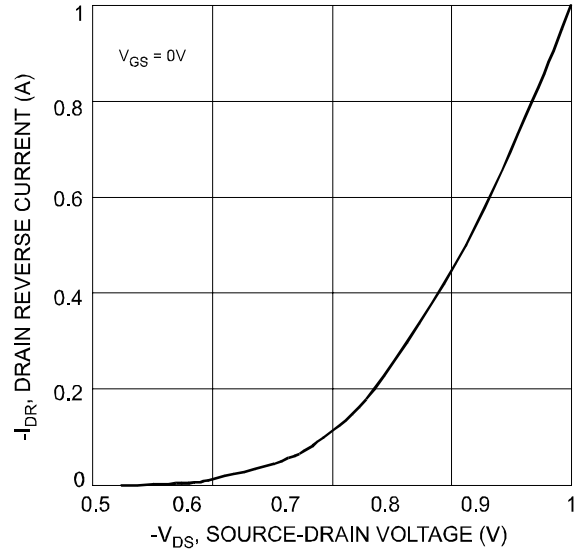


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage

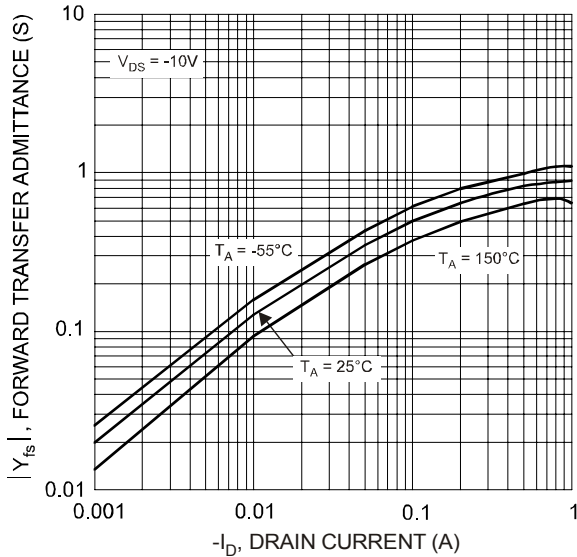


Fig. 9 Forward Transfer Admittance vs. Drain Current

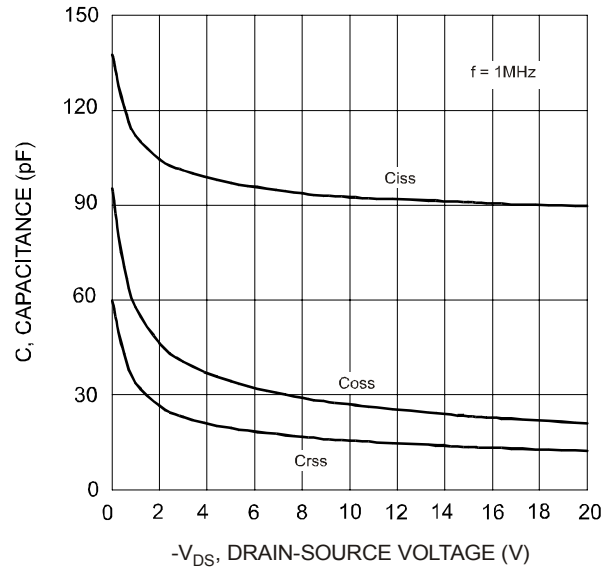


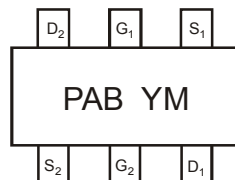
Fig. 10 Typical Capacitance

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2004DWK-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



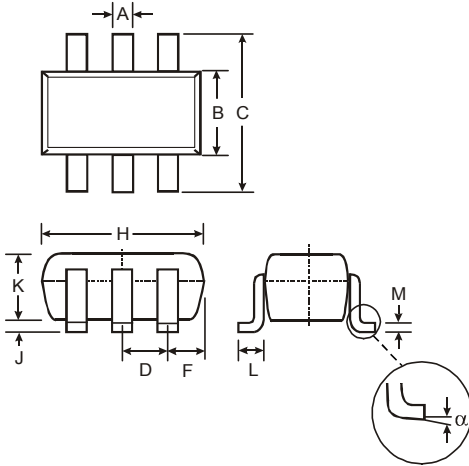
PAB = Marking Code
YM = Date Code Marking
Y = Year ex: U = 2007
M = Month ex: 9 = September

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

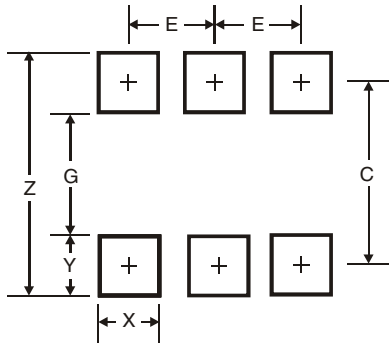
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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